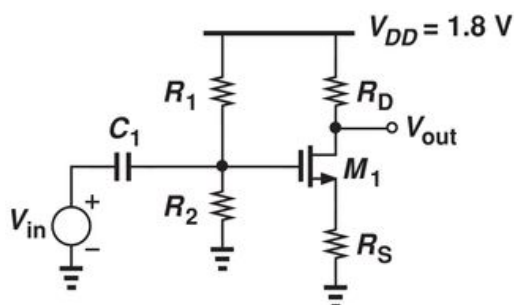


## Digital Electronics Final Homework Due : 4PM, June 21<sup>st</sup>

$\mu_n C_{ox} = 200 \mu A/V^2$ ,  $\mu_p C_{ox} = 100 \mu A/V^2$ , NMOS  $V_{TH} = 0.4 V$ , PMOS  $V_{TH} = -0.4 V$ ,

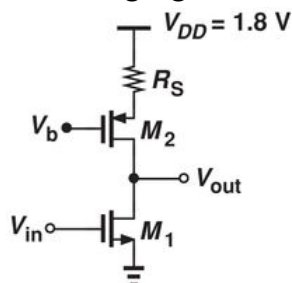
1 (40%) The degenerated stage showing below need to provide a voltage gain of 4 with a power budget of 2 mW. The voltage drop on the  $R_S$  is equal to 200 mV. Assume  $\lambda=0$ , If the overdrive voltage of the transistor is set to 100 mV and  $R_1$  and  $R_2$  must consume 5% of the allocated power, design the circuit by finding (1)  $I_{DS}$  of  $M_1$ , (2)  $R_S$ , (3)  $R_D$ , (4)  $R_2$ , (5)  $R_1$ , (6) (W/L) of  $M_1$ .



2. (40%) A CS stage with a degenerated PMOS current source. The degeneration must raise the output impedance of the current source to about  $10r_{o1}$  such that the voltage gain remains nearly equal to the intrinsic gain of  $M_1$ . Assume  $\lambda=0.1V^{-1}$  for both transistors and a power budget of 2mW.

(a) (20%) If  $V_B=1V$ , determine the values of  $(W/L)_2$  and  $R_S$  so that the impedance seen into the drain of  $M_2$  is equal to  $10 r_{o1}$ .

(b) (10%) Determine  $(W/L)^1$  to achieve a voltage gain of 10.



3. (40%) Design a CG stage shown below such that it can accommodate an output swing of  $500mV_{pp}$  i.e.  $V_{out}$  can fall below its bias value by 250mV without driving  $M_1$  into the triode region. Assume a voltage gain of 4 and an input impedance of  $50\Omega$ . Select  $R_S \approx 10/g_m$  and  $R_1 + R_2 = 20k\Omega$ . Please find the (1)  $g_m$ , (2)  $R_S$ , (3) (W/L) of  $M_1$ , (4)  $R_D$ , (5)  $R_1$ , (6)  $R_2$ , (7)  $I_{DS}$  of  $M_1$ .

(Hint: Since  $M_1$  is biased 250mV away from the triode region, we have  $R_S I_D + V_{GS} - V_{TH} + 250mV = V_{DD} - I_D R_D$ )

